

(19) World Intellectual Property Organization  
International Bureau



(43) International Publication Date  
9 August 2007 (09.08.2007)

PCT

(10) International Publication Number  
**WO 2007/090055 A1**

(51) International Patent Classification:

H01L 27/02 (2006.01) H01L 31/0352 (2006.01)  
H01L 29/36 (2006.01)

(21) International Application Number:

PCT/US2007/061128

(22) International Filing Date: 26 January 2007 (26.01.2007)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:

60/763,643 31 January 2006 (31.01.2006) US

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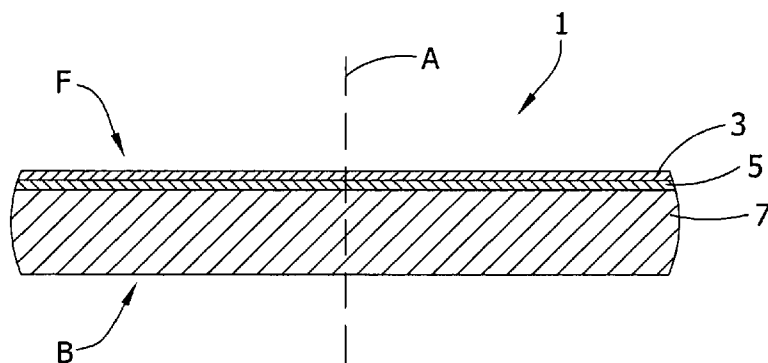
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(81) Designated States (unless otherwise indicated, for every  
kind of national protection available): AE, AG, AL, AM,  
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,  
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,  
GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS,  
JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS,  
LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MY,  
MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS,  
RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN,  
TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

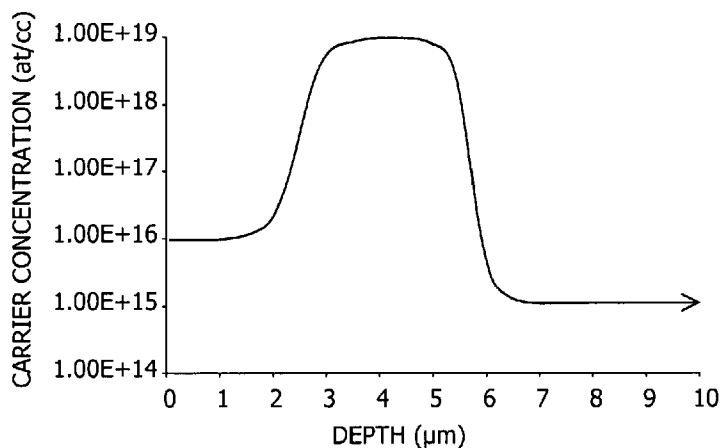
(84) Designated States (unless otherwise indicated, for every  
kind of regional protection available): ARIPO (BW, GH,  
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,  
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),

[Continued on next page]

(54) Title: SEMICONDUCTOR WAFER WITH HIGH THERMAL CONDUCTIVITY



(57) Abstract: This invention generally relates to an epitaxial silicon semiconductor wafer with increased thermal conductivity to transfer heat away from a device layer, while also having resistance to common failure mechanisms, such as latch-up failures and radiation event failures. The semiconductor wafer comprises a lightly-doped device layer, a highly-doped protective layer, and a lightly-doped substrate. The invention is also directed to a process for forming such an epitaxial silicon wafer.





European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

**Published:**

— *with international search report*

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